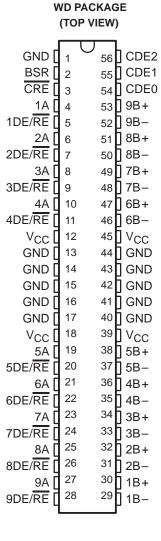
- Nine Differential Channels for the Data and Control Paths of the Differential Small Computer Systems Interface (SCSI) and Intelligent Peripheral Interface (IPI-2)
- Meets or Exceeds the Requirements of ANSI Standard RS-485 and ISO 8482:1987(E)
- Packaged in 380-mil Fine Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacing
- Designed to Operate at 10 Million Transfers Per Second
- Low Disabled Supply Current 1.4 mA Typical
- Thermal Shutdown Protection
- Power-Up/Power-Down Glitch Protection
- Positive and Negative Output Current Limiting
- Open-Circuit Fail-Safe Receiver Design

description

The SN55LBC976 is a 9-channel differential transceiver based on the SN55LBC176 LinASIC™ cell. Use of TI's LinBiCMOS™† process technology allows the power reduction necessary to integrate nine differential transceivers. On-chip enabling logic makes this device applicable for the data path (eight data bits plus parity) and the control path (nine bits) for both the Small Computer Systems Interface (SCSI) and the Intelligent Peripheral Interface (IPI-2) standard data interfaces.



The switching speed and testing capabilities of the SN55LBC976 are sufficient to transfer data over the data bus at 10 million transfers per second. Each of the nine channels conforms to the requirements of the ANSI RS-485 and ISO 8482:1987(E) standards referenced by ANSI X3.129-1986 (IPI), ANSI X3.131-1993 (SCSI-2), and the proposed SCSI-3 standards.

The SN55LBC976 is characterized for operation from -55°C to 125°C.



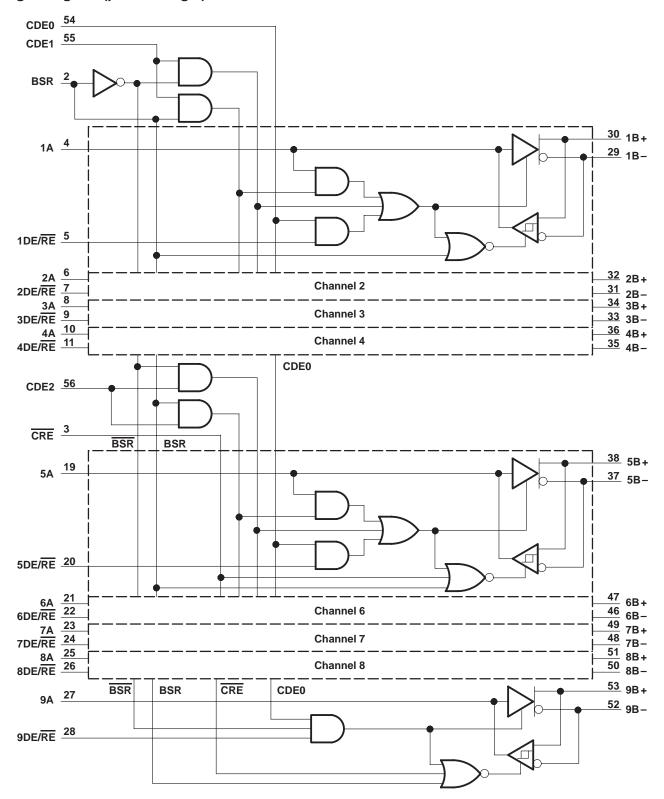
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

† Patent pending

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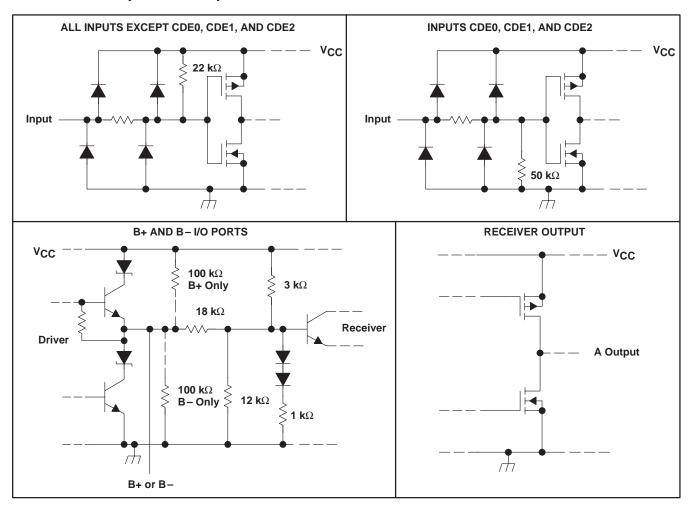
logic diagram (positive logic)†



† For additional logic diagrams, see Application Information, Table 1, and Figures 7 through 44.



schematics of inputs and outputs



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC} (see Note 1)	0.3 V to 7 V
Bus voltage range	–10 V to 15 V
Data I/O and control (A-side) voltage range	–0.3 V to 7 V
Continuous total power dissipation	internally limited
Operating free-air temperature range, T _A	–55°C to 125°C
Storage temperature range, T _{stq}	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to GND.



trecommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, V _{CC}	4.75	5	5.25	V	
Valtage at any hus terminal (congretally or common mode). Ve. Ve. or Ve.	erminal (separately or common-mode), V _O , V _I , or V _{IC}			12	V
voltage at any bus terminal (separately of common-mode), vo, vi, or vic				-7	٧
High-level input voltage, V _{IH}	All except B+ and B-	2			V
Low-level input voltage, V _{IL}	All except B+ and B-			0.8	V
High lovel output ourrent leve	B+ or B-			-60	mA
High-level output current, I _{OH}	A			-8	mA
Low level output current lev	B+ or B-			60	mA
Low-level output current, I _{OL}	А			8	mA
Operating free-air temperature, T _A		-55		125	°C

device electrical characteristics over recommended ranges of operating conditions (unless otherwise noted)

	PARAMETE	:R	TEST C	ONDITIONS	MIN	TYP [†]	MAX	UNIT
	High-level input current	BSR, A, DE/RE, and CRE		V _{IH} = 2 V			-200	μΑ
'ін	nigii-levei iliput current	CDE0, CDE1, and CDE2	See Figure 3	VIH = 2 V			100	μΑ
	Low-level input current	BSR, A, DE/RE, and CRE	See Figure 3	V 0.8 V			-200	μΑ
IIL.	Low-level input current	CDE0, CDE1, and CDE2		V _I L = 0.8 V			100	μΑ
		All drivers and receivers disabled	BSR and CDE0 at 5 V, Other inputs at 0 V No load, V _{ID} = 5 V, All other inputs at 0 V			1.4	5	mA
ICC	Supply current	All receivers enabled				29	50	mA
		All drivers enabled	BSR at 0 V, All other input	No load, s at 5 V		4.8	15	mA
Co	Bus-port output capacitance		B+ or B-			16		pF
<u> </u>	Davies dissination consistence †		One driver			460		pF
Cpd	C _{pd} Power dissipation capacitance [‡]		One receiver			50		pF

driver electrical characteristics over recommended ranges of operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
IVODI	Differential output voltage	V _{test} = -7 V to 12 V, See Figure 2	1	2		V
los	Output short-circuit current	See Figure 1			±250	mA
loz	High-impedance-state output current	See receiver input cu	urrent			



[†] All typical values are at V_{CC} = 5 V, T_A = 25°C. ‡ C_{pd} determines the no-load dynamic current consumption; I_S = C_{pd} × V_{CC} × f + I_{CC} .

receiver electrical characteristics over recommended ranges of operating conditions (unless otherwise noted)

	PARAMETER		TEST CON	IDITIONS	MIN	TYP†	MAX	UNIT
Vон	High-level output voltage		V _{ID} = 200 mV, See Figure 3	$I_{OH} = -8 \text{ mA},$	2.5			V
VOL	Low-level output voltage		$V_{ID} = -200 \text{ mV},$ See Figure 3	I _{OL} = 8 mA,			0.8	V
			$I_{OH} = -8 \text{ mA},$	See Figure 3			0.2	
V _{IT+}	Positive-going input threshold vo	ltage [‡]	I _{OH} = -8 mA, See Figure 3	$T_A = -55^{\circ}C$,			0.5	V
VIT-	Negative-going input threshold v	oltage	I _{OL} = 8 mA,	See Figure 3	-0.2			V
V _{hys}	Receiver input hysteresis (VIT+	- V _{IT−})				45		mV
			V _I = 12 V, Other input at 0 V,	V _{CC} = 5 V, See Figure 3		0.7	1.5	mA
	Description of support	D. and D	V _I = 12 V, Other input at 0 V,	V _{CC} = 0 V, See Figure 3		0.8	1.5	mA
11	Receiver input current	B+ and B-	$V_I = -7 \text{ V},$ Other input at 0 V,	V _{CC} = 5 V, See Figure 3		-0.5	-1	mA
			$V_I = -7 \text{ V},$ Other input at 0 V,	V _{CC} = 0 V, See Figure 3		-0.4	-1	mA
107	High-impedance-state output cui	rent	See Figure 3	$V_O = GND$			-200	μА
loz	r ngri impedance-state output cui	-impedance-state output current		AO = ACC			50	μΑ

driver switching characteristics over recommended operating conditions (unless otherwise noted) (see Figure 4)

	PARAMETER		NDITIONS	MIN	TYP	MAX	UNIT
1.5	Differential delay time, high-to-low-level output (t _{dDH}) or			4		30	ns
^t dD	low-to-high-level output (t _{dDL})	V _C C = 5 V,	T _A = 25°C	9		17	115
	Skew limit, the maximum difference in propagation delay times					12	20
tsk(lim)	between any two drivers on any two devices	$V_{CC} = 5 V$,	See Note 2			8	ns
t _{sk(p)}	Pulse skew (t _{dDL} - t _{dDH})					6	ns
t _t	Transition time (t _r or t _f)				10		ns

[†] All typical values are at $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

NOTE 2: This specification applies to any 5°C band within the operating temperature range.



[†] All typical values are at V_{CC} = 5 V, T_A = 25°C. ‡ This parameter is not tested to meet RS-485 or SCSI standards at –55°C.

receiver switching characteristics over recommended operating conditions (see Figure 5) (unless otherwise noted)

	PARAMETER		TEST CONDITIONS		TYP [†]	MAX	UNIT
	Propagation delay time, high-to-low-level output (tpHL) or			16		36	20
^t pd	low-to-high-level output (t _{PLH})	$V_{CC} = 5 V$	T _A = 25°C	21		31	ns
+ \	Skew limit, the maximum difference in propagation delay times					12	ns
^t sk(lim)	between any two drivers on any two devices	$V_{CC} = 5 V$,	See Note 2			9	115
+ + , ,)	Pulse skew (tpHi - tpi H)				2	6	ns
t _{sk(p)}	Fulse skew ([iPHL - iPLHI])	$T_A = -55^{\circ}C$				10	ns
t _t	Transition time $(t_f \text{ or } t_f)$				3		ns

[†] All typical values are at V_{CC} = 5 V, T_A = 25°C.

NOTE 2: This specification applies to any 5°C band within the operating temperature range.

transceiver switching characteristics over recommended operating conditions

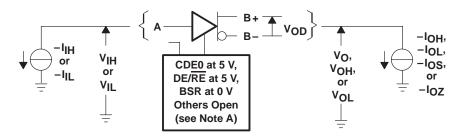
	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
ten(RXL)	Enable time, transmit-to-receive to low-level output			180*	ns
ten(RXH)	Enable time, transmit-to-receive to high-level output			180*	ns
ten(TXL)	Enable time, receive-to-transmit to low-level output	See Figure 6		110*	ns
ten(TXH)	Enable time, receive-to-transmit to high-level output			110*	ns
t _{su}	Setup time, CDE0, CDE1, CDE2, BSR, or CRE to active input(s) or output(s)		180*		ns

^{*} This parameter is not production tested.

thermal characteristics

PARAMETER		TEST CONI	MIN	TYP	MAX	UNIT	
$R_{\theta JA}$	Junction-to-free-air thermal resistance	Board mounted,	No air flow		95.4		°C/W
$R_{\theta JC}$	Junction-to-case thermal resistance				5.67		°C/W

PARAMETER MEASUREMENT INFORMATION



NOTE A: For the I_{OZ} test, the BSR input is at 5 V and all others are at 0 V.

Figure 1. Driver Test Circuit and Input Conditions



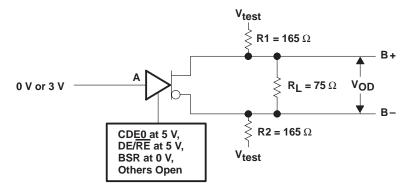
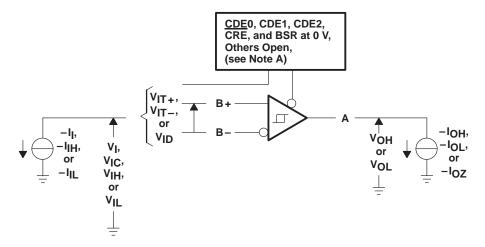
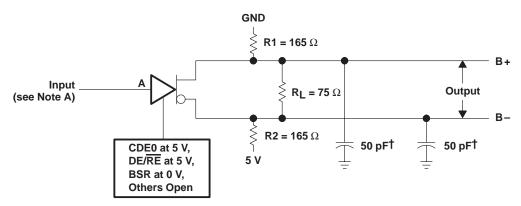


Figure 2. Driver V_{OD} Test Circuit



NOTE A: For the $I_{\mbox{OZ}}$ measurement, BSR is at 5 V and CDE0, CDE1, and CDE2 are at 0 V.

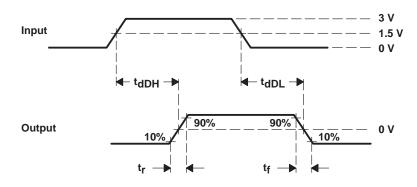
Figure 3. Receiver Test Circuit and Input Conditions



† Includes probe and jig capacitance.

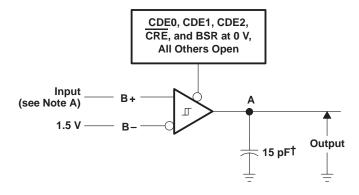
NOTE A: The input is provided by a pulse generator with an output of 0 V to 3 V, PRR of 1 MHz, 50% duty cycle, t_r and t_f < 6 ns, and Z_Q = 50 Ω .

TEST CIRCUIT



VOLTAGE WAVEFORMS

Figure 4. Driver Test Circuit and Voltage Waveforms



† Includes probe and jig capacitance.

NOTE A: The input is provided by a pulse generator with an output of 0 to 3 V, PRR of 1 MHz, 50% duty cycle, t_f and t_f < 6 ns, and Z_O = 50 Ω .

TEST CIRCUIT

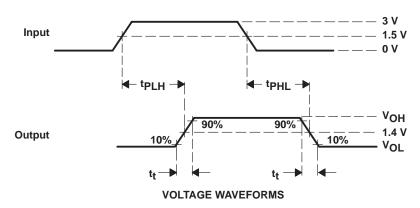
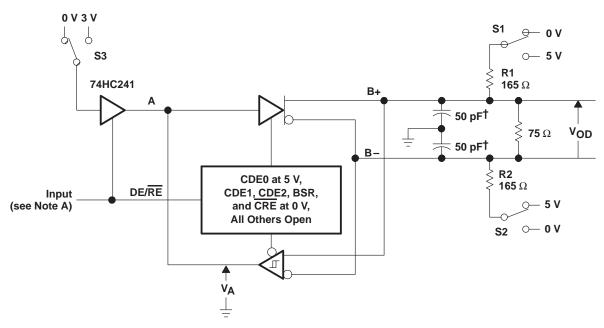


Figure 5. Receiver Test Circuit and Voltage Waveforms



† Includes probe and jig capacitance.

NOTE A: The input is provided by a pulse generator with an output of 0 V to 3 V, PRR of 1 MHz, 50% duty cycle, t_f and t_f < 6 ns, and t_f = 50 t_f .

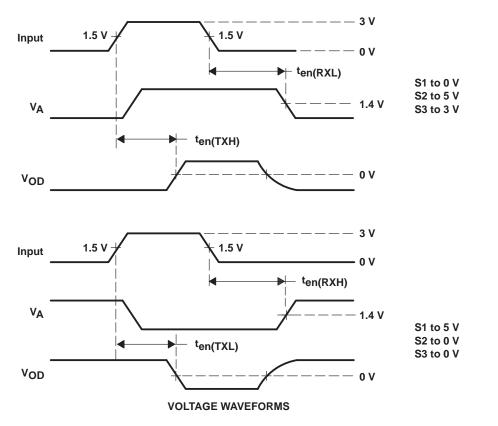
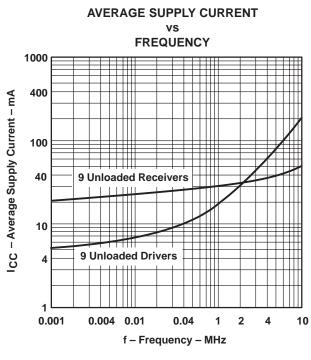


Figure 6. Enable Time Test Circuit and Voltage Waveforms





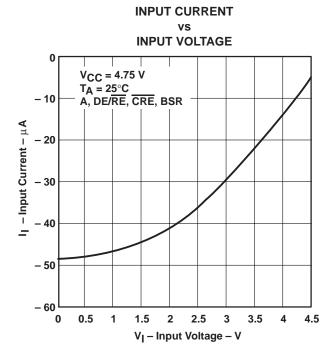


Figure 7

Figure 8

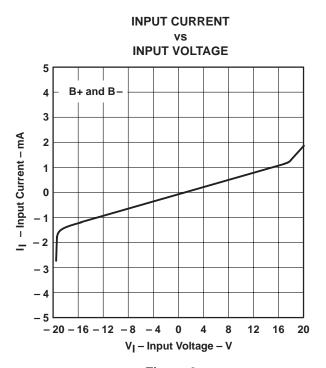
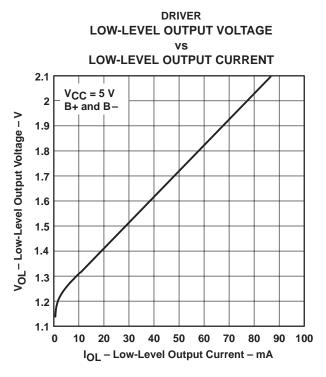


Figure 9



DRIVER HIGH-LEVEL OUTPUT VOLTAGE **HIGH-LEVEL OUTPUT CURRENT** B+ and B-4.75 VOH - High-Level Output Voltage - mV 4.5 4.25 V_{CC} = 5.25 V 3.75 $V_{CC} = 5 V$ 3.5 3.25 2.75 $V_{CC} = 4.75 V$ 2.5 -10 -20 -30 -40 -50 -60 -70 -80 -90IOH - High-Level Output Current - mA

Figure 10

Figure 11

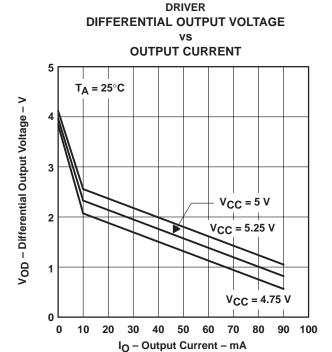


Figure 12



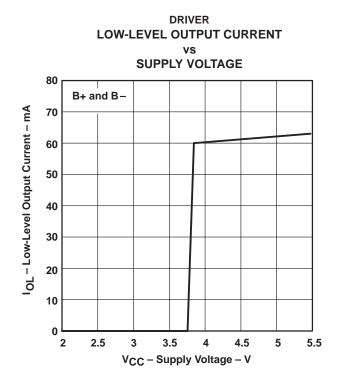


Figure 13

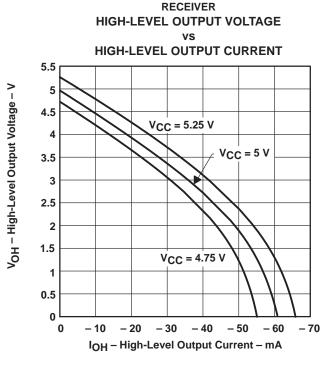


Figure 15

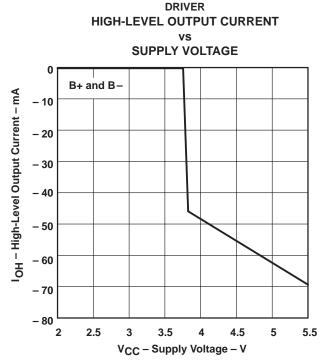


Figure 14

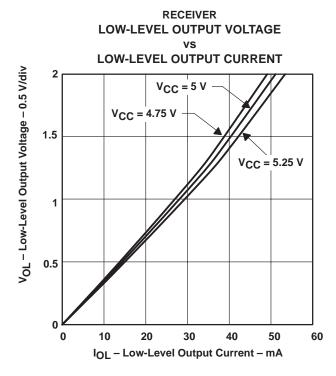
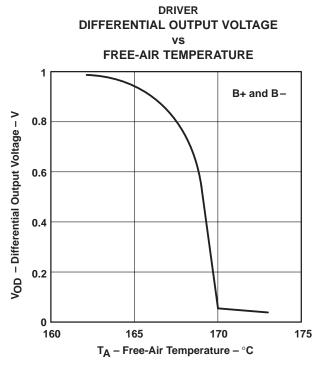


Figure 16



PROPAGATION DELAY TIME FREE-AIR TEMPERATURE 35 t PHL or t PLH - Propagation Delay Time - ns 30 V_{CC} = 4.75 V V_{CC} = 5.25 V 25 20 15 10 5 0 - 25 25 50 75 100 T_A – Free-Air Temperature – ${}^{\circ}C$

RECEIVER

Figure 17

Figure 18

DRIVER PROPAGATION DELAY TIME vs FREE-AIR TEMPERATURE

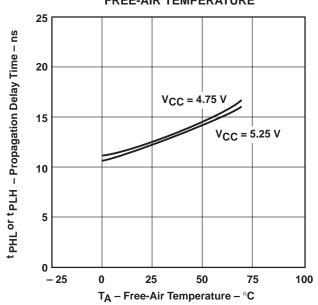


Figure 19



Table 1. Typical Signal and Terminal Assignments

SIGNAL	TERMINAL	SCSI DATA	SCSI CONTROL	IPI DATA	IPI CONTROL
CDE0	54	DIFFSENSE	DIFFSENSE	VCC	Vcc
CDE1	55	GND	GND	XMTA, XMTB	GND
CDE2	56	GND	GND	XMTA, XMTB	SLAVE/MASTER
BSR	2	GND	GND	GND, BSR	GND
CRE	3	GND	GND	GND	Vcc
1A	4	DB0, DB8	ATN	AD7, BD7	NOT USED
1DE/RE	5	DBE0, DBE8	INIT EN	GND	GND
2A	6	DB1, DB9	BSY	AD6, BD6	NOT USED
2DE/RE	7	DBE1, DBE9	BSY EN	GND	GND
3A	8	DB2, DB10	ACK	AD5, BD5	SYNC IN
3DE/RE	9	DBE2, DBE10	INIT EN	GND	GND
4A	10	DB3, DB11	RST	AD4, BD4	SLAVE IN
4DE/RE	11	DBE3, DBE11	GND	GND	GND
5A	19	DB4, DB12	MSG	AD3, BD3	NOT USED
5DE/RE	20	DBE4, DBE12	TARG EN	GND	GND
6A	21	DB5, DB13	SEL	AD2, BD2	SYNC OUT
6DE/RE	22	DBE5, DBE13	SEL EN	GND	GND
7A	23	DB6, DB14	C/D	AD1, BD1	MASTER OUT
7DE/RE	24	DBE6, DBE14	TARG EN	GND	GND
8A	25	DB7, DB15	REQ	AD0, BD0	SELECT OUT
8DE/RE	26	DBE7, DBE15	TARG EN	GND	GND
9A	27	DBP0, DBP1	I/O	AP, BP	ATTENTION IN
9DE/RE	28	DBPE0, DBPE1	TARG EN	XMTA, XMTB	VCC

ABBREVIATIONS:

DBn, data bit n, where $n = (0,1, \dots, 15)$

DBEn, data bit n enable, where $n = (0,1, \dots, 15)$

DBP0, parity bit for data bits 0 through 7 or IPI bus A

DBPE0, parity bit enable for P0

DBP1, parity bit for data bits 8 through 15 or IPI bus B

DBPE1, parity bit enable for P1

ADn or BDn, IPI Bus A – Bit n (ADn) or Bus B – Bit n (BDn), where n = (0,1, ..., 7)

AP or BP, IPI parity bit for bus A or bus B

XMTA or XMTB, transmit enable for IPI bus A or B

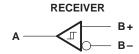
BSR, bit significant response

INIT EN, common enable for SCSI initiator mode

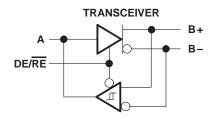
TARG EN, common enable for SCSI target mode

NOTE 3: Signal inputs are shown as active high. When only active-low inputs are available, logic inversion is accomplished by reversing the B+ and B- connecter terminal assignments.

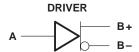
Function Tables



INP	UTS	OUTPUT
B+†	в-†	Α
L	Н	L
Н	L	Н



I	OUTPUTS					
DE/RE	Α	B+†	в-†	Α	B+	B-
L	_	L	Н	L	_	_
L	_	Н	L	Н	_	-
Н	L	_	_	_	L	Н
Н	Н	_	_	_	Н	L



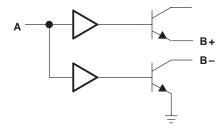
INPUT	OUTPUTS	
Α	B+	B-
L	L	Н
Н	Н	L

DRIVER WITH ENABLE



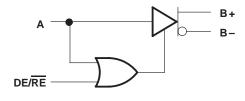
INPUTS		OUTPUTS	
DE/RE	Α	B+	B-
L	L	Z	Z
L	Н	Z	Z
Н	L	L	Н
Н	Н	Н	L

WIRED-OR DRIVER



INPUT	OUTPUTS	
Α	B+	B-
L	Z	Z
Н	Н	L

TWO-ENABLE INPUT DRIVER

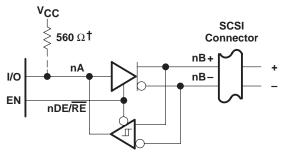


INPUTS		OUTPUTS	
DE/RE	Α	B+	B-
L	L	Z	Z
L	Н	Н	L
Н	L	L	Н
Н	Н	Н	L

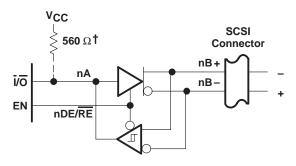
H = high level, L = low level, X = irrelevant, Z = high impedance (off)

† An H in this column represents a voltage that is 200 mV higher than the other bus input. An L represents a voltage that is 200 mV lower than the other bus input. Any voltage less than 200 mV results in an indeterminate receiver output.

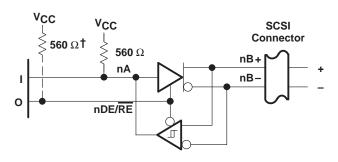




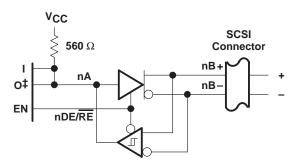
(a) ACTIVE-HIGH BIDIRECTIONAL I/O WITH SEPARATE ENABLE



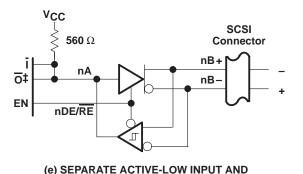
(b) ACTIVE-LOW BIDIRECTIONAL I/O WITH SEPARATE ENABLE



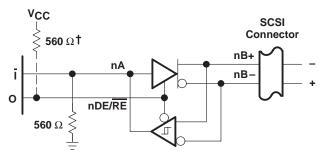
(c) WIRED-OR DRIVER AND ACTIVE-HIGH INPUT



(d) SEPARATE ACTIVE-HIGH INPUT, OUTPUT, **AND ENABLE**



OUTPUT AND ACTIVE-HIGH ENABLE



(f) WIRED-OR DRIVER AND ACTIVE-LOW INPUT

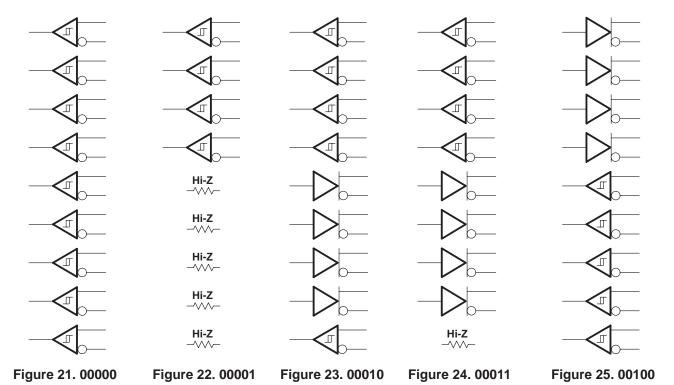
† Must be open-drain or 3-state output NOTE A: The BSR, CRE, A, and DE/RE inputs have internal pullups. CDE0, CDE1, and CDE2 have internal pulldowns.

Figure 20. Typical SCSI Transceiver Connections

[†] When this resistor is 0 Ω , the circuit is open drain.

channel logic configurations with control input logic

The following logic diagrams show the positive-logic representation for all combinations of control inputs. The control inputs are from MSB to LSB; the BSR, CDE0, CDE1, CDE2, and \overline{CRE} bit values are shown below the diagrams. Channel 1 is at the top of the logic diagrams; channel 9 is at the bottom of the logic diagrams.



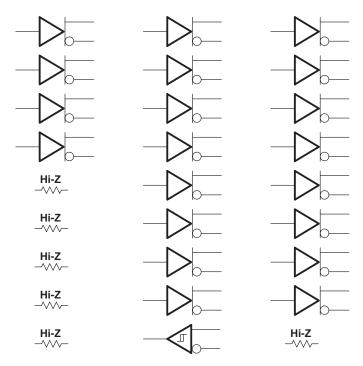
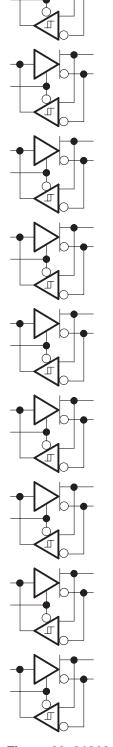


Figure 26. 00101 Figure 27. 00110 Figure 28. 00111



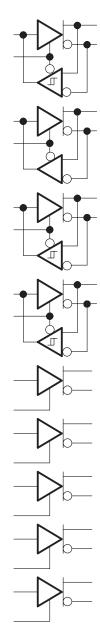
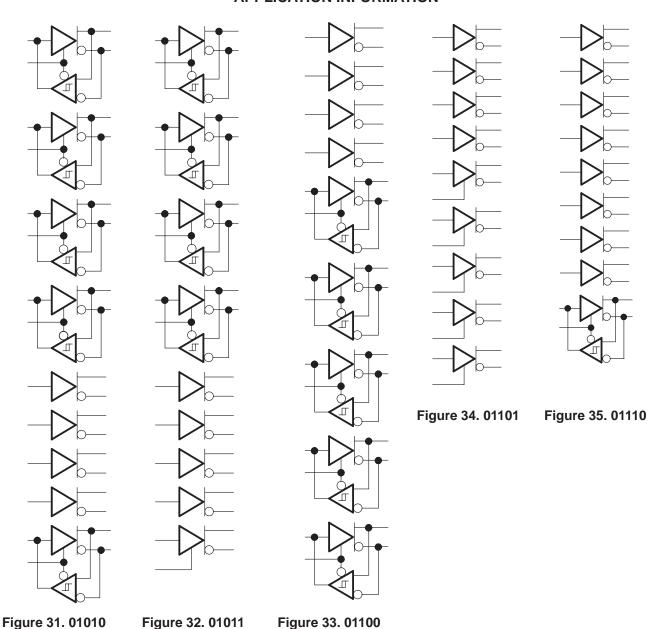
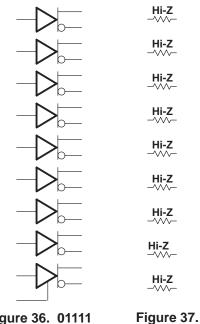


Figure 30. 01001

Figure 29. 01000







10000 and 10001

Figure 36. 01111

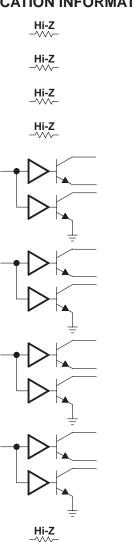


Figure 38. 10010 and 10011

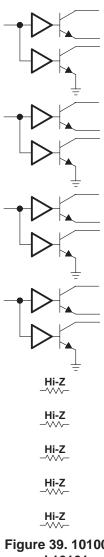


Figure 39. 10100 and 10101

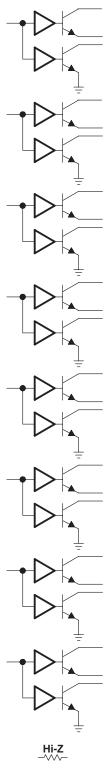


Figure 40. 10110 and 10111



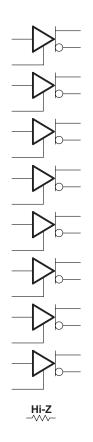


Figure 41. 11000 and 11001

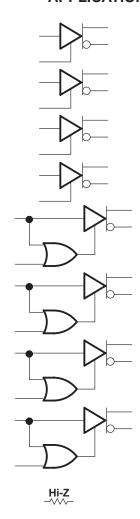


Figure 42. 11010 and 11011

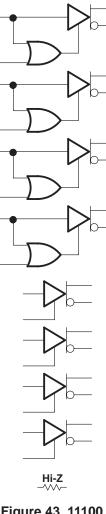


Figure 43. 11100 and 11101

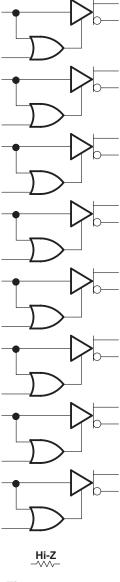


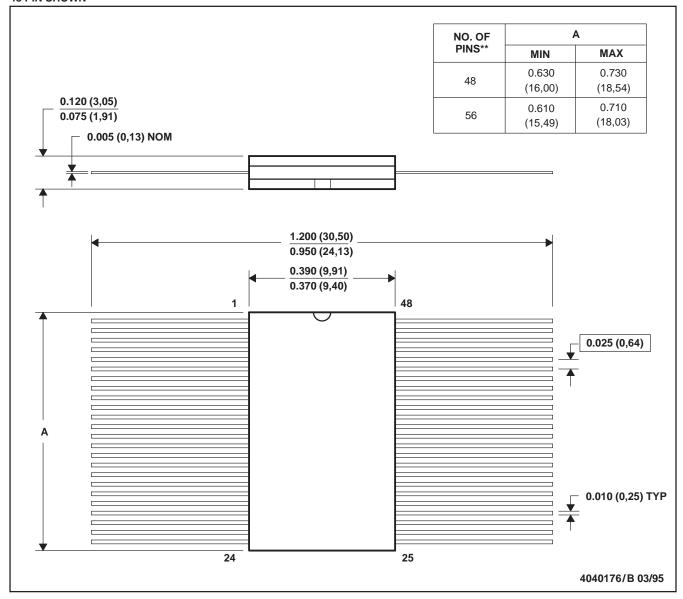
Figure 44. 11110 and 11111

MECHANICAL INFORMATION

WD (R-GDFP-F**)

CERAMIC DUAL FLATPACK

48 PIN SHOWN



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for pin identification only
- E. Falls within MIL-STD-1835: GDFP1-F48 and JEDEC MO-146AA GDFP1-F56 and JEDEC MO-146AB



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